

SURFACE MOUNT SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50-1000V CURRENT: 1.0 A

Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: JEDEC SOD-123FL molded plastic body over passivated chip
- Terminals : Plated axial leads,
- solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position : Any
- Weight:0.0007 ounce, 0.02 grams



Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic		Symbol	S1AFL	S1BFL	S1DFL	S1GFL	S1JFL	S1KFL	S1MFL	Unit
		Marking	1A	1B	1D	1G	1J	1K	1M	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage		VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current $@T_L = 100^{\circ}C$		lo	1.0							А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)		IFSM	30							A
Forward Voltage	@I _F = 1.0A	Vfm				1.10				V
	@T _A = 25°C @T _A = 125°C	I RM	5.0 200					μA		
Reverse Recovery Time (Note 1)		trr	2.5							μS
Typical Junction Capacitance (Note 2)		Cj	15							pF
Typical Thermal Resistance (Note 3)		$R_{ heta}JL$	30							K/W
Operating and Storage Temperature Range		Tj, TSTG	-65 to +175							°C

Note: 1. Measured with I_{F} = 0.5A, I_{R} = 1.0A, I_{rr} = 0.25A,

2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

3. Mounted on P.C. Board with 8.0mm² land area.









